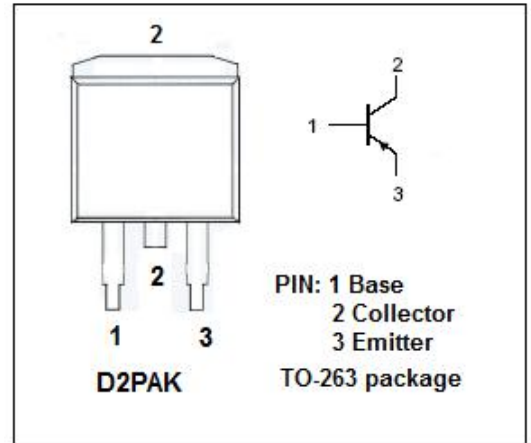


isc Silicon PNP Power Transistor
KSB834W
DESCRIPTION

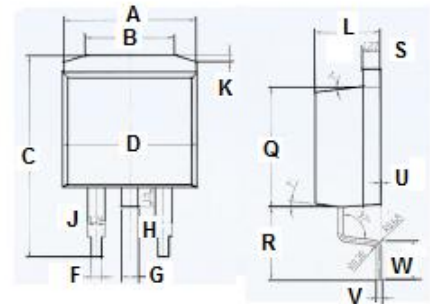
- Complement to KSD880W
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Low frequency power amplifier


ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

| SYMBOL | PARAMETER | VALUE | UNIT |
|-----------|---|---------|------------------|
| V_{CBO} | Collector-Base Voltage | -60 | V |
| V_{CEO} | Collector-Emitter Voltage | -60 | V |
| V_{EBO} | Emitter-Base Voltage | -7 | V |
| I_C | Collector Current-Continuous | -3 | A |
| P_C | Total Power Dissipation @ $T_a=25^\circ\text{C}$ | 1.5 | W |
| P_C | Total Power Dissipation @ $T_c=25^\circ\text{C}$ | 30 | W |
| T_J | Junction Temperature | 150 | $^\circ\text{C}$ |
| T_{stg} | Storage Temperature Range | -55~150 | $^\circ\text{C}$ |



| DIM | mm | |
|-----|-------|-------|
| | MIN | MAX |
| A | 10 | |
| B | 6.6 | 6.8 |
| C | 15.23 | 15.25 |
| D | 10.15 | 10.17 |
| F | 0.76 | 0.78 |
| G | 1.26 | 1.28 |
| H | 1.4 | 1.6 |
| J | 1.33 | 1.35 |
| K | 0.4 | 0.6 |
| L | 4.6 | 4.8 |
| Q | 8.69 | 8.71 |
| R | 5.28 | 5.30 |
| S | 1.26 | 1.28 |
| U | 0.0 | 0.2 |
| V | 0.37 | 0.39 |
| W | 2.80 | 2.82 |

isc Silicon PNP Power Transistor

KSB834W

ELECTRICAL CHARACTERISTICS

T_c=25°C unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP | MAX | UNIT |
|----------------------|--------------------------------------|---|-----|-----|------|------|
| V _{CE(sat)} | Collector-Emitter Saturation Voltage | I _C = -3.0A; I _B = -300mA | | | -1 | V |
| V _{BE(on)} | Base-Emitter On Voltage | I _C = -0.5A; V _{CE} =-5V | | | -1 | V |
| I _{CBO} | Collector Cutoff Current | V _{CB} = -60V; I _E = 0 | | | -100 | μ A |
| I _{EBO} | Emitter Cutoff Current | V _{EB} = -7V; I _C = 0 | | | -100 | μ A |
| h _{FE1} | DC Current Gain | I _C =- 0.5A; V _{CE} =- 5V | 60 | | 200 | |
| h _{FE2} | DC Current Gain | I _C = -3A; V _{CE} = -5V | 20 | | | |
| f _T | Current-Gain—Bandwidth Product | I _C = -0.5A; V _{CE} = -5V | | 9 | | MHz |
| C _{ob} | Collector output capacitance | V _{CB} =-10V ,I _E =0,f=1MHz | | 150 | | pF |

◆ h_{FE-1} Classifications

| | |
|--------|---------|
| O | Y |
| 60-120 | 100-200 |

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